



ON Semiconductor®

# FQB47P06

## P-Channel QFET® MOSFET

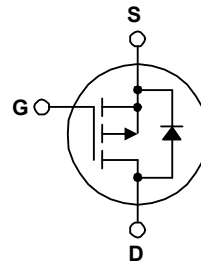
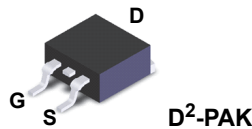
-60 V, -47 A, 26 mΩ

### Description

This P-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- -47 A, -60 V,  $R_{DS(on)} = 26 \text{ m}\Omega$  (Max.) @  $V_{GS} = .10 \text{ V}$ ,  $I_D = -23.5 \text{ A}$
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQB47P06TM-AM002	Unit
V <sub>DSS</sub>	Drain-Source Voltage	-60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	-47	A
	- Continuous (T <sub>C</sub> = 100°C)	-33.2	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	-188	A
V <sub>GSS</sub>	Gate-Source Voltage	± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	820	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	-47	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	16	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *	3.75	W
	Power Dissipation (T <sub>C</sub> = 25°C)	160	W
	- Derate above 25°C	1.06	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	FQB47P06TM-AM002	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	0.94	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

FQB47P06 — P-Channel QFET® MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB47P06TM-AM002	FQB47P06	D <sup>2</sup> -PAK	Tape and Reel	330 mm	24 mm	800 units

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.06	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{DS} = -48\text{ V}, T_C = 150^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -23.5\text{ A}$	--	0.021	0.026	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -30\text{ V}, I_D = -23.5\text{ A}$	--	21	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2800	3600	pF
$C_{oss}$	Output Capacitance		--	1300	1700	pF
$C_{rss}$	Reverse Transfer Capacitance		--	320	420	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}, I_D = -23.5\text{ A},$ $R_G = 25\ \Omega$	--	50	110	ns
$t_r$	Turn-On Rise Time		--	450	910	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	210	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	195	400
$Q_g$	Total Gate Charge	$V_{DS} = -48\text{ V}, I_D = -47\text{ A},$ $V_{GS} = -10\text{ V}$	--	84	110	nC
$Q_{gs}$	Gate-Source Charge		--	18	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	44	--

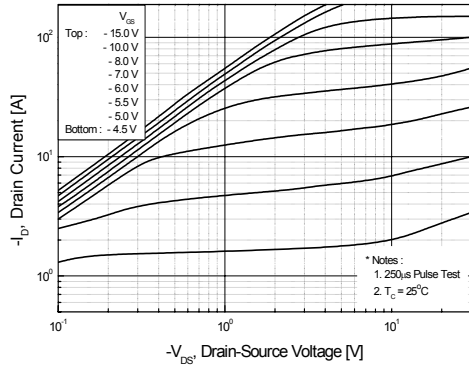
### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	-47	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-188	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -47\text{ A}$	--	--	-4.0	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -47\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	130	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	0.55	--	$\mu\text{C}$

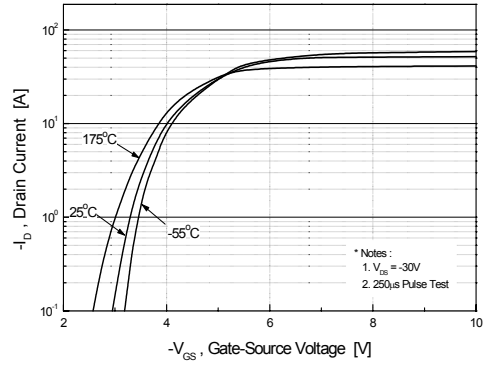
#### Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2.  $L = 0.43\text{ mH}, I_{AS} = -47\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq -47\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

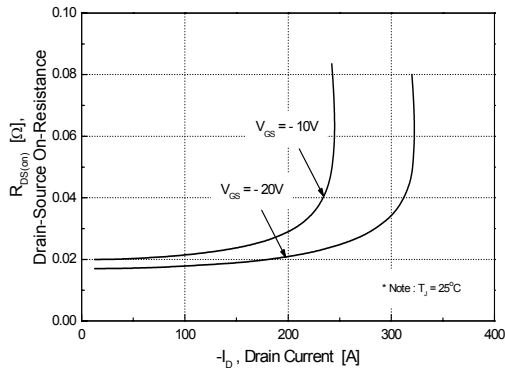
## Typical Characteristics



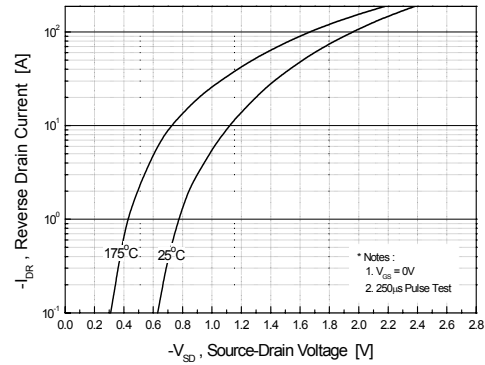
**Figure 1. On-Region Characteristics**



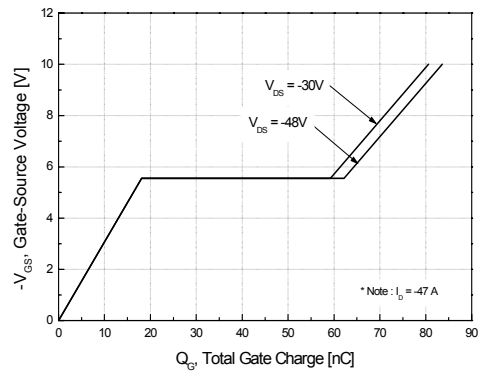
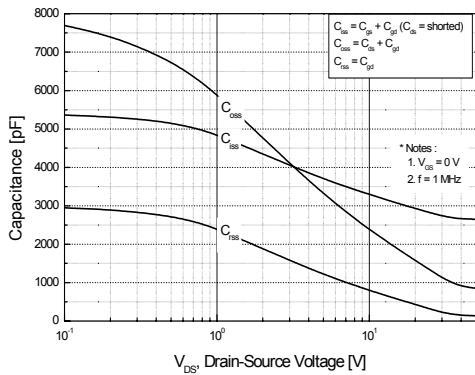
**Figure 2. Transfer Characteristics**



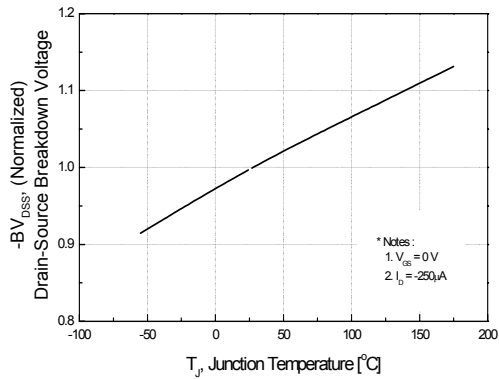
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



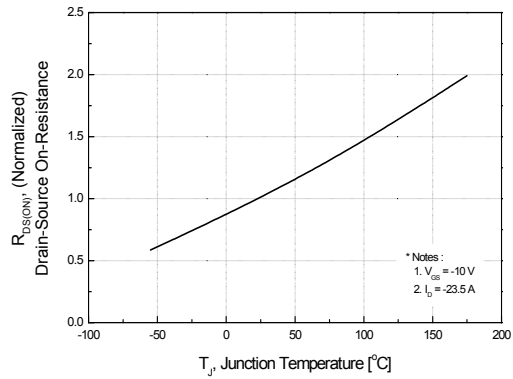
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



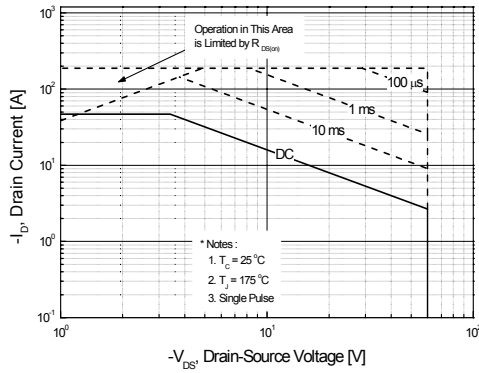
**Typical Characteristics** (Continued)



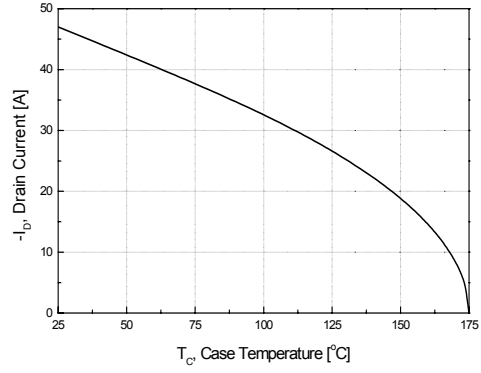
**Figure 7. Breakdown Voltage Variation vs. Temperature**



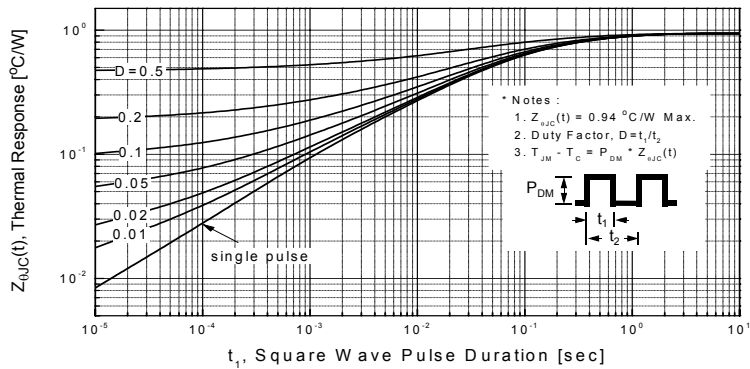
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

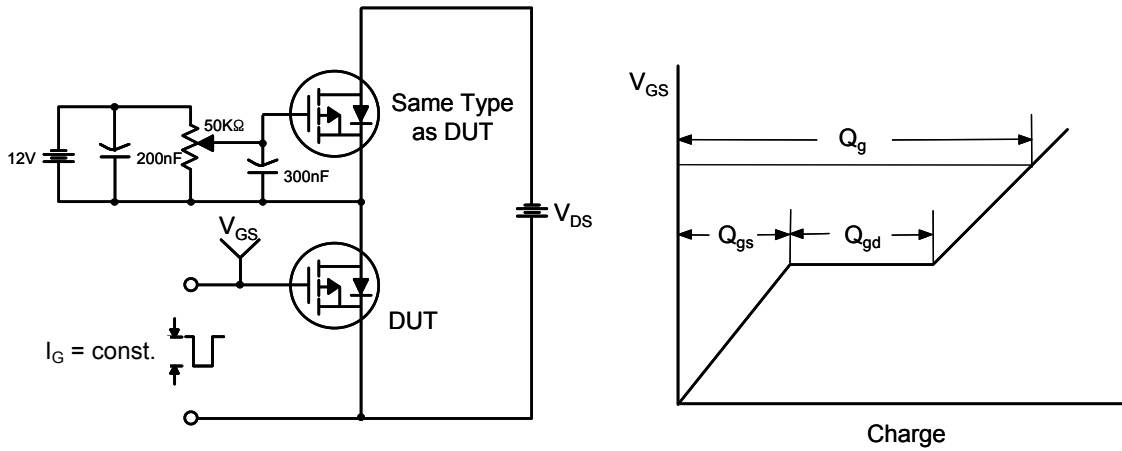


Figure 12. Gate Charge Test Circuit & Waveform

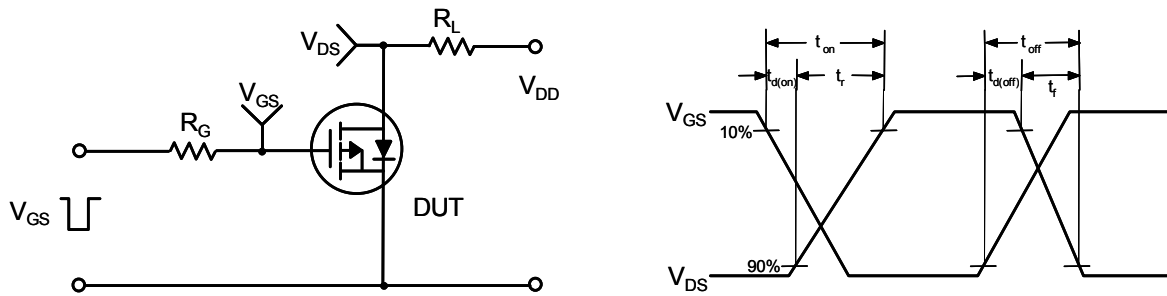


Figure 13. Resistive Switching Test Circuit & Waveforms

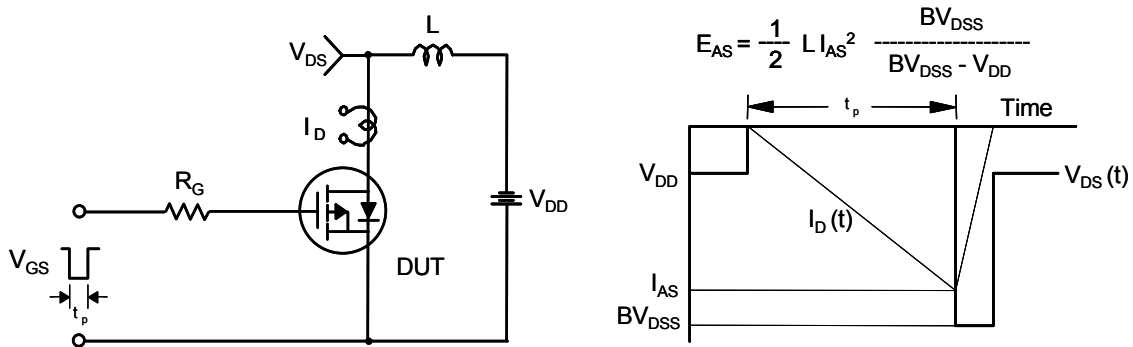


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

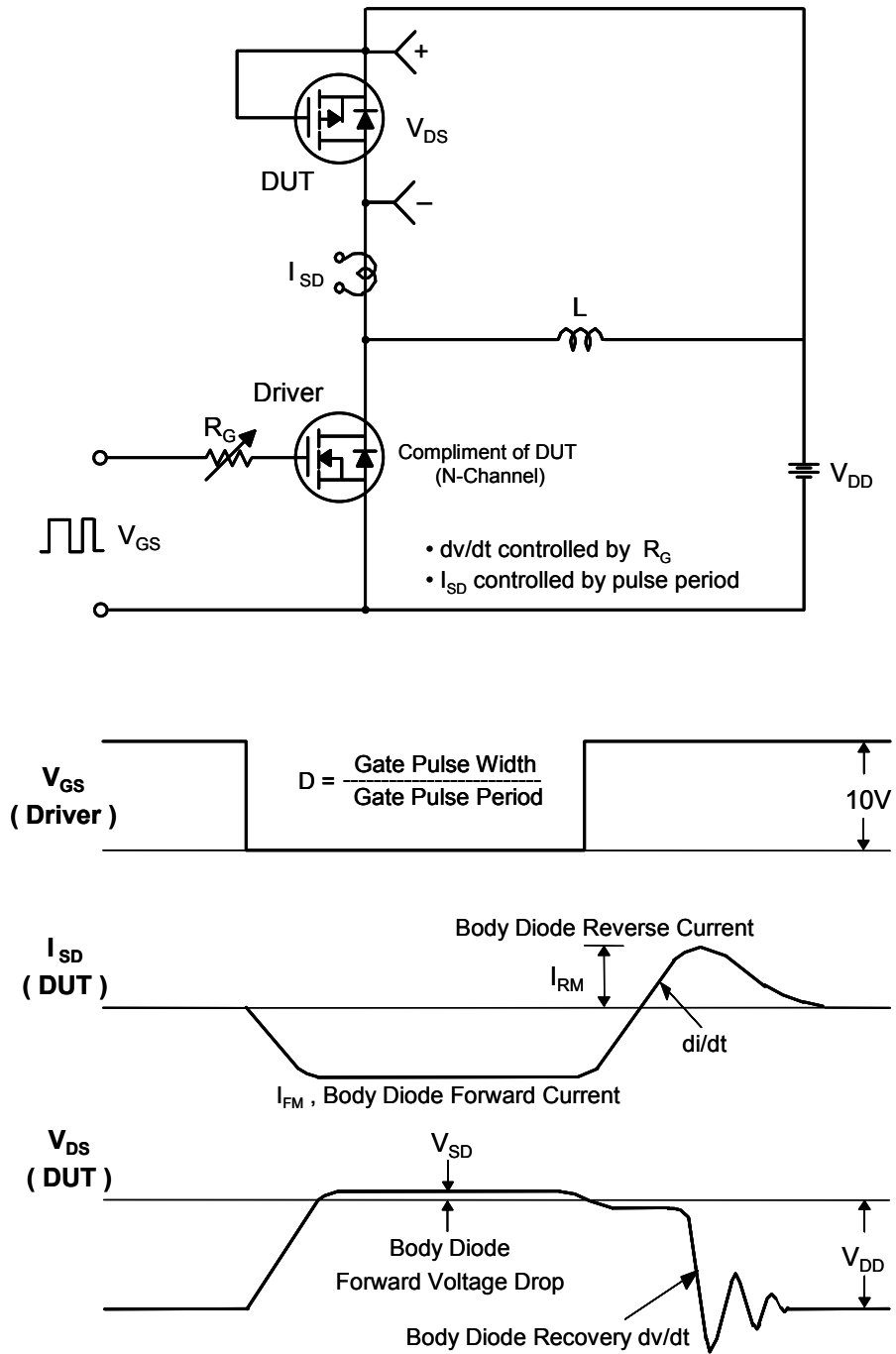
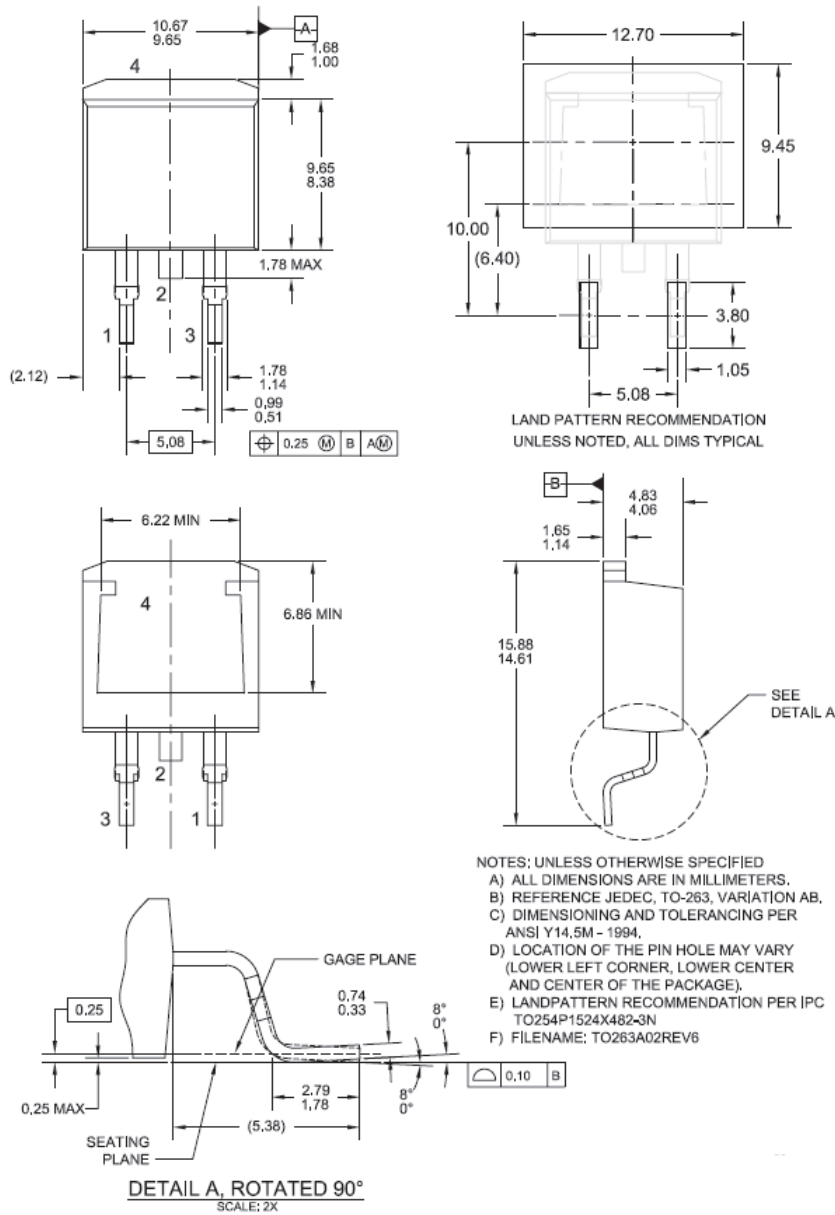


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

## Mechanical Dimensions



**Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount**

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